# CPH3362

# **Power MOSFET** –100V, 1.7Ω, –0.7A, Single P-Channel



#### Features

• On-resistance R<sub>DS</sub>(on)1=1.3Ω (typ)

• Halogen free compliance

• 4V drive

### **Specifications**

#### **Absolute Maximum Ratings** at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		-100	V
Gate to Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-0.7	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	-2.8	А
Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V\*", so please take care when handling.

\* Machine Model

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Thermal Resistance Ratings**

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	$R_{ hetaJA}$	125	°C/W

#### **Electrical Characteristics** at Ta = 25°C

Deveration				Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μA
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.3A		1.0		S
	R <sub>DS</sub> (on)1	I <sub>D</sub> =-0.7A, V <sub>GS</sub> =-10V		1.3	1.7	Ω
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =-0.3A, V <sub>GS</sub> =-4.5V		1.4	1.96	Ω
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.3A, V <sub>GS</sub> =-4V		1.45	2.1	Ω
Input Capacitance	Ciss			142		pF
Output Capacitance	Coss	V <sub>DS</sub> =–20V, f=1MHz		12		pF
Reverse Transfer Capacitance	Crss			7.3		pF

Continued on next page.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

Continued from preceding page.						
Parameter	Sumbol	Conditions min		Value		
Parameter	Symbol		min	Тур	max	Unit
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit		3.9		ns
Rise Time	tr			3.4		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)			28		ns
Fall Time	tf			12		ns
Total Gate Charge	Qg	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-0.7A		3.7		nC
Gate to Source Charge	Qgs			0.37		nC
Gate to Drain "Miller" Charge	Qgd			0.86		nC
Forward Diode Voltage	VSD	I <sub>S</sub> =-0.7A, V <sub>GS</sub> =0V		-0.83	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Ordering & Package Information**

Device	Package	Shipping	note
CPH3362-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

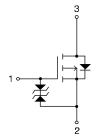
# Packing Type:TL



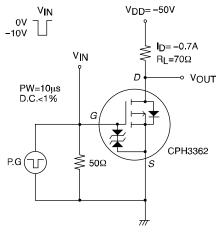


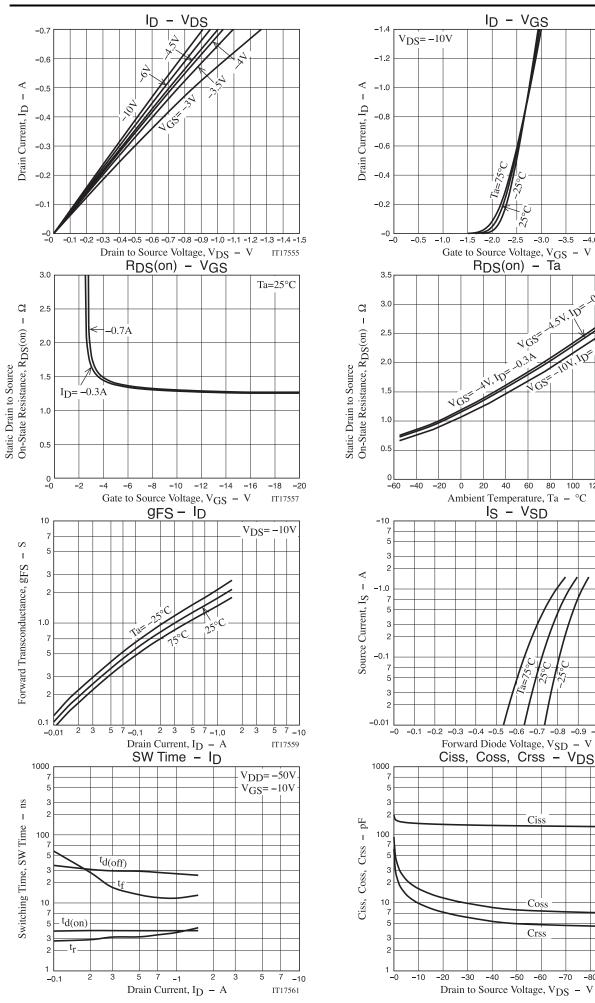


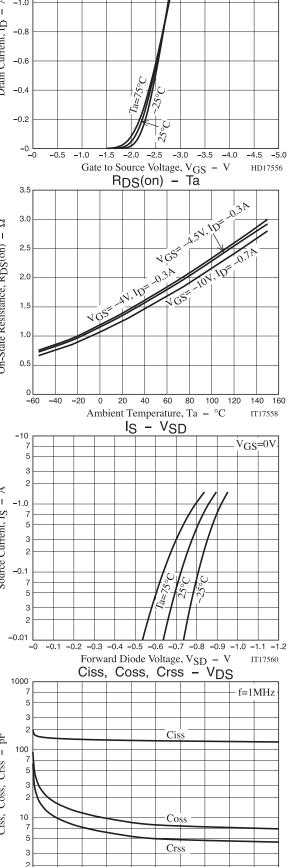
# **Electrical Connection**



# **Switching Time Test Circuit**







ID - VGS

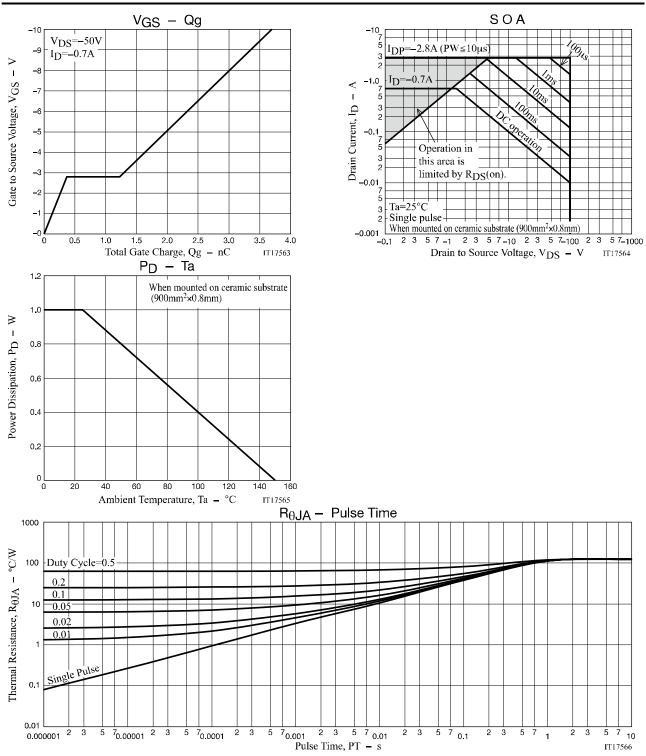
-90 -100

IT17562

-80

-50 -60 -70

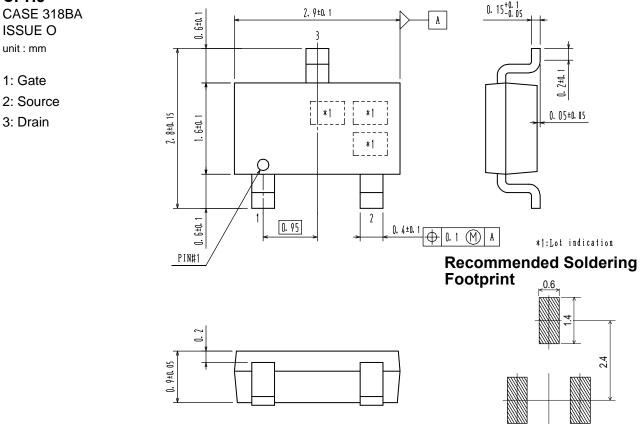
-40



### **Package Dimensions**

CPH3362-TL-W

#### CPH3



Note on usage : Since the CPH3362 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the des

0.95

0.95

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: CPH3362-TL-W